

# Abstracts

## Extraction of FET Model Noise-Parameters from Measurement

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A. Riddle. "Extraction of FET Model Noise-Parameters from Measurement." 1991 MTT-S International Microwave Symposium Digest 91.3 (1991 Vol. III [MWSYM]): 1113-1116.

A rigorous noise-parameter extraction technique for MESFETs and HEMTs is presented. This technique analytically extracts the FET current noise-parameters (P, R, and C) from the measured S- and noise-parameters. This procedure does not require curve fitting, optimization, or simplified noise models. The matrix-based extraction method is derived and shown to be reasonably robust. The sensitivity of this technique to experimental error is also discussed.

[Return to main document.](#)